

Marilena Vivona

List of Publications by Year in descending order

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52
papers

768
citations

687363

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552781

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g-index

52
all docs

52
docs citations

52
times ranked

662
citing authors

#	ARTICLE	IF	CITATIONS
1	Recent advances on dielectrics technology for SiC and GaN power devices. Applied Surface Science, 2014, 301, 9-18.	6.1	130
2	Radiation hardening techniques for Er/Yb doped optical fibers and amplifiers for space application. Optics Express, 2012, 20, 8457.	3.4	99
3	SiO ₂ /4H-SiC interface doping during post-deposition-annealing of the oxide in N ₂ O or POCl ₃ . Applied Physics Letters, 2013, 103, .	3.3	70
4	Thermal stability of the current transport mechanisms in Ni-based Ohmic contacts on n- and p-implanted 4H-SiC. Semiconductor Science and Technology, 2014, 29, 075018.	2.0	45
5	Comparative study of gate oxide in 4H-SiC lateral MOSFETs subjected to post-deposition-annealing in N ₂ O and POCl ₃ . Applied Physics A: Materials Science and Processing, 2014, 115, 333-339.	2.3	35
6	Design of Radiation-Hardened Rare-Earth Doped Amplifiers Through a Coupled Experiment/Simulation Approach. Journal of Lightwave Technology, 2013, 31, 1247-1254.	4.6	32
7	Near interface traps in SiO ₂ /4H-SiC metal-oxide-semiconductor field effect transistors monitored by temperature dependent gate current transient measurements. Applied Physics Letters, 2016, 109, .	3.3	31
8	Selective Doping in Silicon Carbide Power Devices. Materials, 2021, 14, 3923.	2.9	31
9	Electrical and structural properties of surfaces and interfaces in Ti/Al/Ni Ohmic contacts to p-type implanted 4H-SiC. Applied Surface Science, 2017, 420, 331-335.	6.1	30
10	Ti/Al/W Ohmic contacts to p-type implanted 4H-SiC. Journal of Applied Physics, 2015, 118, .	2.5	27
11	Temperature-dependent Fowler-Nordheim electron barrier height in SiO ₂ /4H-SiC MOS capacitors. Materials Science in Semiconductor Processing, 2018, 78, 38-42.	4.0	27
12	Ti/Al-based contacts to p-type SiC and GaN for power device applications. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600357.	1.8	17
13	Influence of Ce codoping and H ₂ pre-loading on Er/Yb-doped fiber: Radiation response characterized by Confocal Micro-Luminescence. Journal of Non-Crystalline Solids, 2011, 357, 1963-1965.	3.1	14
14	Influence of Ce^{3+} Codoping on the Photoluminescence Excitation Channels of Phosphosilicate Yb/Er-Doped Glasses. IEEE Photonics Technology Letters, 2012, 24, 509-511.	2.5	14
15	Barrier height tuning in Ti/4H-SiC Schottky diodes. Solid-State Electronics, 2021, 186, 108042.	1.4	13
16	Metal/Semiconductor Contacts to Silicon Carbide: Physics and Technology. Materials Science Forum, 0, 924, 339-344.	0.3	12
17	Ni Schottky barrier on heavily doped phosphorous implanted 4H-SiC. Journal Physics D: Applied Physics, 2021, 54, 445107.	2.8	12
18	Electrical properties of inhomogeneous tungsten carbide Schottky barrier on 4H-SiC. Journal Physics D: Applied Physics, 2021, 54, 055101.	2.8	12

#	ARTICLE	IF	CITATIONS
19	Electrical Characteristics of Schottky Contacts on Ge-Doped 4H-SiC. Materials Science Forum, 0, 778-780, 706-709.	0.3	11
20	Ge Mediated Surface Preparation for Twin Free 3C-SiC Nucleation and Growth on Low Off-Axis 4H-SiC Substrate. ECS Journal of Solid State Science and Technology, 2014, 3, P285-P292.	1.8	10
21	Characterization of SiO ₂ /SiC Interfaces Annealed in N ₂ O or POCl ₃ . Materials Science Forum, 0, 778-780, 623-626.	0.3	10
22	Properties of Al ₂ O ₃ thin films deposited on 4H-SiC by reactive ion sputtering. Materials Science in Semiconductor Processing, 2019, 93, 290-294.	4.0	10
23	Active dopant profiling and Ohmic contacts behavior in degenerate n-type implanted silicon carbide. Applied Physics Letters, 2020, 117, .	3.3	8
24	Materials and Processes for Schottky Contacts on Silicon Carbide. Materials, 2022, 15, 298.	2.9	8
25	Radiation effects on rare-earth doped optical fibers. Proceedings of SPIE, 2010, , .	0.8	7
26	Non-destructive characterization of rare-earth-doped optical fiber preforms. Optics Letters, 2018, 43, 4907.	3.3	7
27	Effect of germanium doping on electrical properties of n-type 4H-SiC homoepitaxial layers grown by chemical vapor deposition. Journal of Applied Physics, 2016, 120, .	2.5	6
28	Electrical properties of SiO ₂ /SiC interfaces on 2°-off axis 4H-SiC epilayers. Applied Surface Science, 2016, 364, 892-895.	6.1	5
29	Electrical characterization of trapping phenomena at SiO ₂ /SiC and SiO ₂ /GaN in MOS-based devices. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600366.	1.8	5
30	Electrical evolution of W and WC Schottky contacts on 4H-SiC at different annealing temperatures. Semiconductor Science and Technology, 2022, 37, 015012.	2.0	5
31	Radiation hardening techniques for rare-earth-based optical fibers and amplifiers. Proceedings of SPIE, 2012, , .	0.8	4
32	Radiation effects on fiber amplifiers: design of radiation tolerant Yb/Er-based devices. , 2011, , .		3
33	Comparative Study of the Current Transport Mechanisms in Ni ₂ Si Ohmic Contacts on n- and p-Type Implanted 4H-SiC. Materials Science Forum, 0, 778-780, 665-668.	0.3	3
34	Study of Ti/Al/Ni Ohmic Contacts to p-Type Implanted 4H-SiC. Materials Science Forum, 0, 924, 377-380.	0.3	3
35	Temperature and time dependent electron trapping in Al ₂ O ₃ thin films onto AlGaIn/GaN heterostructures. Applied Surface Science, 2022, 579, 152136.	6.1	3
36	Coupled experiment/simulation approach for the design of radiation-hardened rare-earth doped optical fibers and amplifiers. , 2011, , .		2

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37	X-Ray Irradiation on 4H-SiC MOS Capacitors Processed under Different Annealing Conditions. Materials Science Forum, 2016, 858, 659-662.	0.3	2
38	Properties of SiO ₂ /4H-SiC Interfaces with an Oxide Deposited by a High-Temperature Process. Materials Science Forum, 2017, 897, 331-334.	0.3	2
39	Instrumentation for Simultaneous Non-Destructive Profiling of Refractive Index and Rare-Earth-Ion Distributions in Optical Fiber Preforms. Instruments, 2018, 2, 23.	1.8	2
40	Temperature-Dependence Study of the Gate Current SiO ₂ /4H-SiC MOS Capacitors. Materials Science Forum, 0, 924, 473-476.	0.3	1
41	X-ray irradiation influence on prototype Er ³⁺ -optical fibers: confocal luminescence study. , 2010, , .		0
42	Nanoscale reliability aspects of insulator onto wide band gap compounds. , 2014, , .		0
43	Probing at Nanoscale Underneath the Gate Oxides in 4H-SiC MOS-Based Devices Annealed in N ₂ and POCl ₃ . Materials Science Forum, 0, 806, 143-147.	0.3	0
44	Ge Assisted 3C-SiC Nucleation and Growth by Vapour Phase Epitaxy on On-Axis 4H-SiC Substrate. Materials Science Forum, 2014, 806, 27-31.	0.3	0
45	Evolution of the Electrical and Structural Properties of Ti/Al/W Contacts to p-Type Implanted 4H-SiC upon Thermal Annealing. Materials Science Forum, 0, 821-823, 428-431.	0.3	0
46	Preliminary Study on the Effect of Micrometric Ge-Droplets on the Characteristics of Ni/4H-SiC Schottky Contacts. Materials Science Forum, 2015, 821-823, 424-427.	0.3	0
47	Processing and Characterization of MOS Capacitors Fabricated on 2°-Off Axis 4H-SiC Epilayers. Materials Science Forum, 0, 858, 663-666.	0.3	0
48	Anomalous Fowler-Nordheim Tunneling through SiO ₂ /4H-SiC Barrier Investigated by Temperature and Time Dependent Gate Current Measurements. Materials Science Forum, 0, 897, 123-126.	0.3	0
49	Radiation hardening of rare-earth doped fiber amplifiers. , 2017, , .		0
50	Non-destructive microscopic characterization of optical fiber preforms. , 2018, , .		0
51	Full non-destructive characterization of doped optical fibre preforms. , 2019, , .		0
52	Ni/Heavily-Doped 4H-SiC Schottky Contacts. Materials Science Forum, 0, 1062, 411-416.	0.3	0